## BAT54WS

## SCHOTTKY BARRIER DIODE

## Features

- Low forward voltage
- Guard ring protected
- Small plastic SMD SOD-323 package


## Applications

- Ultra high-speed switching
- Voltage clamping


## PINNING

| PIN | DESCRIPTION |
| :---: | :--- |
| 1 | Cathode |
| 2 | Anode |



Top View
Marking Code: "S1"
Simplified outline SOD-323 and symbol

- Protection circuits

Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ )

| Parameter | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Reverse Voltage | $\mathrm{V}_{\mathrm{R}}$ | 30 | V |
| Forward Current | $\mathrm{I}_{\mathrm{F}}$ | 200 | mA |
| Repetitive Peak Forward Current | $\mathrm{I}_{\text {FRM }}$ | 300 | mA |
| Peak Forward Surge Current $\left(\mathrm{t}_{\mathrm{p}}=10 \mathrm{~ms}\right)$ | $\mathrm{I}_{\mathrm{FSM}}$ | 600 | mA |
| Power Dissipation | $\mathrm{P}_{\mathrm{D}}$ | 230 | mW |
| Thermal Resistance from Junction Ambient | $\mathrm{R}_{\mathrm{thJA}}$ | 500 | $\mathrm{~K} / \mathrm{W}$ |
| Junction Temperature | $\mathrm{T}_{\mathrm{J}}$ | 125 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\text {stg }}$ | $-65 \mathrm{to}+150$ | ${ }^{\circ} \mathrm{C}$ |

## Characteristics at $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Max. | Unit |
| :---: | :---: | :---: | :---: |
| $\begin{aligned} & \text { Forward Voltage } \\ & \text { at } I_{F}=0.1 \mathrm{~mA} \\ & \text { at } I_{F}=1 \mathrm{~mA} \\ & \text { at } \mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA} \\ & \text { at } \mathrm{I}_{F}=30 \mathrm{~mA} \\ & \text { at } \mathrm{I}_{F}=100 \mathrm{~mA}\end{aligned}$ | $V_{F}$ | $\begin{aligned} & 240 \\ & 320 \\ & 400 \\ & 500 \\ & 800 \end{aligned}$ | mV |
| Reverse Current at $\mathrm{V}_{\mathrm{R}}=25 \mathrm{~V}$ | $\mathrm{I}_{\mathrm{R}}$ | 2 | $\mu \mathrm{A}$ |
| Total Capacitance at $\mathrm{V}_{\mathrm{R}}=1 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ | $\mathrm{C}_{\mathrm{T}}$ | 10 | pF |
| Reverse Recovery Time at $I_{F}=10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{R}}=6 \mathrm{~V}, \mathrm{I}_{\mathrm{R}}=10 \mathrm{~mA}, \mathrm{R}_{\mathrm{L}}=100 \Omega$ | $\mathrm{t}_{\mathrm{rr}}$ | 6 | ns |

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Figure 1．Typical Fonward Voltage Fonward Current at Various Temperatures


Figure 2．Typical Capacitance ${ }^{\circ} \mathrm{C}$ vs．Reverse Applied Voltage $\mathrm{V}_{\mathrm{R}}$

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## PACKAGE OUTLINE



